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ON Semiconductor NUD3105DMT1

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NUD3105D

Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays from 3.0 V to 5.0 V Rail
- Capable of Driving Relay Coils Rated up to 2.5 W at 5.0 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low V_{DS(on)} Reduces System Current Drain
- Pb-Free Package is Available

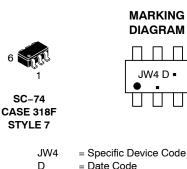
Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers
- Automotive: 5.0 V Driven Relays, Motor Controls, Power Latches, Lamp Drivers



http://onsemi.com

Relay, Inductive Load Driver 0.5 Amp, 8.0 V Clamp



= Date Code

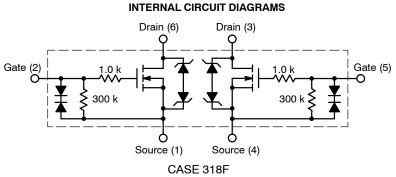
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3105DMT1	SC-74	3000/Tape & Reel
NUD3105DMT1G	SC-74 (Pb-Free)	3000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



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MAXIMUM RATINGS (T_J = 25° C unless otherwise specified)

Symbol	Rating	Value	Unit
V _{DSS}	Drain to Source Voltage – Continuous	6.0	V _{dc}
V _{GS}	Gate to Source Voltage – Continuous	6.0	V _{dc}
Ι _D	Drain Current – Continuous	500	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy ($T_{Jinitial} = 25^{\circ}C$)	50	mJ
TJ	Junction Temperature	150	°C
T _A	Operating Ambient Temperature	-40 to 85	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
P _D	Total Power Dissipation (Note 1) Derating Above 25°C	380 1.5	mW mW/°C
R_{\thetaJA}	Thermal Resistance Junction-to-Ambient	329	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

This device contains ESD protection and exceeds the following tests: Human Body Model 2000 V per MIL_STD-883, Method 3015. Machine Model Method 200 V.

TYPICAL ELECTRICAL CHARACTERISTICS (T_J = $25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Тур	Мах	Unit	
OFF CHARACTERISTICS						
V _{BRDSS}	Drain to Source Sustaining Voltage (Internally Clamped) (I _D = 10 mA)	6.0	8.0	9.0	V	
B _{VGSO}	I _g = 1.0 mA	-	-	8.0	V	
I _{DSS}	Drain to Source Leakage Current ($V_{DS} = 5.5 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 25^{\circ}\text{C}$) ($V_{DS} = 5.5 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 85^{\circ}\text{C}$)			15 15	μΑ	
I _{GSS}	$ \begin{array}{l} \mbox{Gate Body Leakage Current} \\ \mbox{(V}_{GS}=3.0 \mbox{ V}, \mbox{V}_{DS}=0 \mbox{ V}) \\ \mbox{(V}_{GS}=5.0 \mbox{ V}, \mbox{V}_{DS}=0 \mbox{ V}) \end{array} $	5.0 _		35 65	μΑ	
ON CHARA	CTERISTICS	-	-	-	-	
V _{GS(th)}	Gate Threshold Voltage (V _{GS} = V _{DS} , I _D = 1.0 mA)	0.8	1.2	1.4	V	

V _{GS(th)}	Gate Threshold Voltage $(V_{GS} = V_{DS}, I_D = 1.0 \text{ mA})$ $(V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}, T_J = 85^{\circ}\text{C})$	0.8 0.8	1.2 -	1.4 1.4	v
R _{DS(on)}	$\label{eq:linear} \begin{array}{l} \text{Drain to Source On-Resistance} \\ (I_D = 250 \text{ mA, } V_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA, } V_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA, } V_{GS} = 5.0 \text{ V}) \\ (I_D = 500 \text{ mA, } V_{GS} = 3.0 \text{ V, } T_J = 85^\circ\text{C}) \\ (I_D = 500 \text{ mA, } V_{GS} = 5.0 \text{ V, } T_J = 85^\circ\text{C}) \end{array}$	- - - -	- - - -	1.2 1.3 0.9 1.3 0.9	Ω
I _{DS(on)}	Output Continuous Current ($V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}$) ($V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_J = 85^{\circ}\text{C}$)	300 200	400 -		mA
9FS	Forward Transconductance (V _{OUT} = 5.0 V, I _{OUT} = 0.25 A)	350	570	-	mMhos



TYPICAL ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS					
C _{iss}	Input Capacitance $(V_{DS} = 5.0 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 10 \text{ kHz})$	-	25	-	pF
C _{oss}	Output Capacitance $(V_{DS} = 5.0 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$		37	-	pF
C _{rss}	Transfer Capacitance $(V_{DS} = 5.0 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	-	8.0	-	pF

SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Тур	Max	Units
	Propagation Delay Times:				nS
t _{PHL}	High to Low Propagation Delay; Figure 1 (5.0 V)	-	25	-	
t _{PLH}	Low to High Propagation Delay; Figure 1 (5.0 V)	-	80	-	
t _{PHL}	High to Low Propagation Delay; Figure 1 (3.0 V)	-	44	-	
t _{PLH}	Low to High Propagation Delay; Figure 1 (3.0 V)	-	44	-	
	Transition Times:				nS
t _f	Fall Time; Figure 1 (5.0 V)	-	23	-	
tr	Rise Time; Figure 1 (5.0 V)	-	32	-	
t _f	Fall Time; Figure 1 (3.0 V)	-	53	-	
t _r	Rise Time; Figure 1 (3.0 V)	-	30	-	-

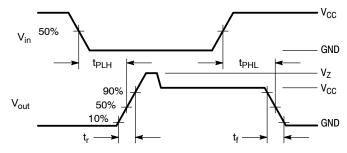


Figure 1. Switching Waveforms



NUD3105D

TYPICAL CHARACTERISTICS

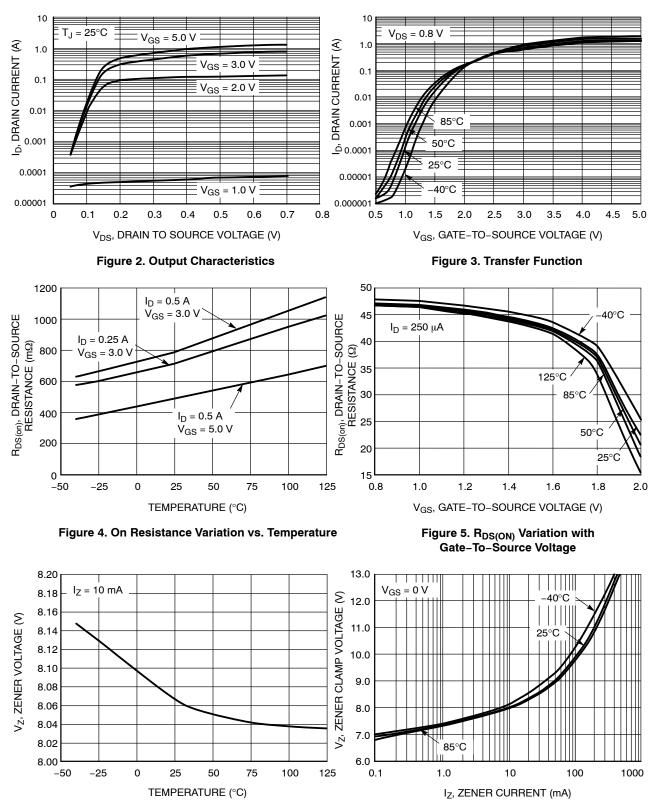


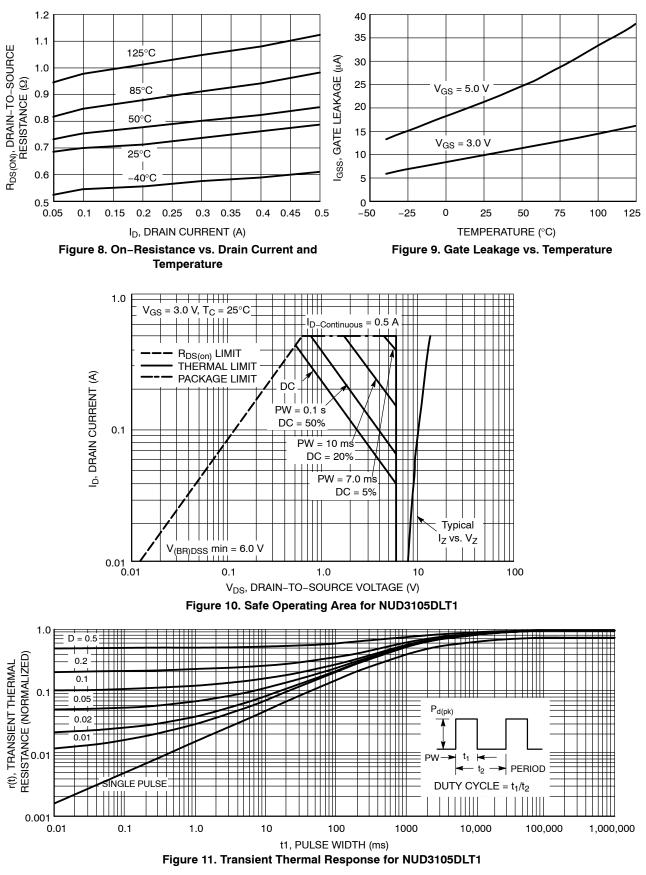
Figure 6. Zener Voltage vs. Temperature

Figure 7. Zener Clamp Voltage vs. Zener Current



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TYPICAL CHARACTERISTICS

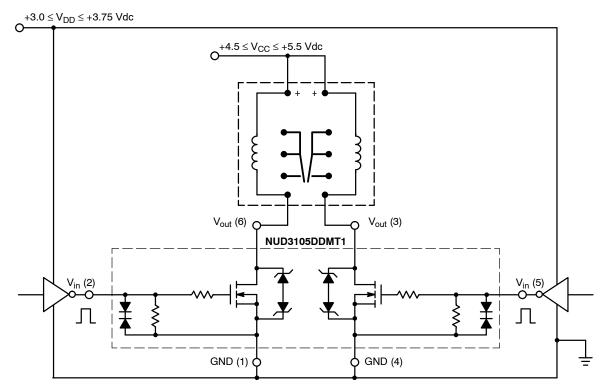




Designing with this Data Sheet

- 1. Determine the maximum inductive load current (at max V_{CC} , min coil resistance & usually minimum temperature) that the NUD3105D will have to drive and make sure it is less than the max rated current.
- 2. For pulsed operation, use the Transient Thermal Response of Figure 11 and the instructions with it to determine the maximum limit on transistor power dissipation for the desired duty cycle and temperature range.
- 3. Use Figures 10 and 11 with the SOA notes to insure that instantaneous operation does not push the device beyond the limits of the SOA plot.

- 4. Verify that the circuit driving the gate will meet the $V_{GS(th)}$ from the Electrical Characteristics table.
- 5. Using the max output current calculated in step 1, check Figure 7 to insure that the range of Zener clamp voltage over temperature will satisfy all system & EMI requirements.
- 6. Use I_{GSS} and I_{DSS} from the Electrical Characteristics table to insure that "OFF" state leakage over temperature and voltage extremes does not violate any system requirements.
- 7. Review circuit operation and insure none of the device max ratings are being exceeded.



APPLICATIONS DIAGRAMS

Figure 12. A 200 mW, 5.0 V Dual Coil Latching Relay Application with 3.0 V Level Translating Interface



NUD3105D

Max Continuous Current Calculation

for TX2–5V Relay, R1 = 178 Ω Nominal @ R_A = 25°C Assuming ±10% Make Tolerance, R1 = 178 Ω * 0.9 = 160 Ω Min @ T_A = 25°C T_C for Annealed Copper Wire is 0.4%/°C R1 = 160 Ω * [1+(0.004) * (-40°-25°)] = 118 Ω Min @ -40°C I₀ Max = (5.5 V Max - 0.25V) /118 Ω = 45 mA

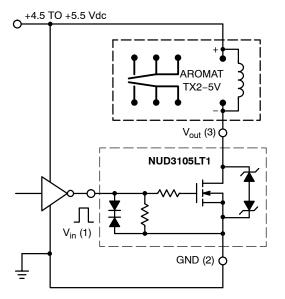


Figure 13. A 140 mW, 5.0 V Relay with TTL Interface

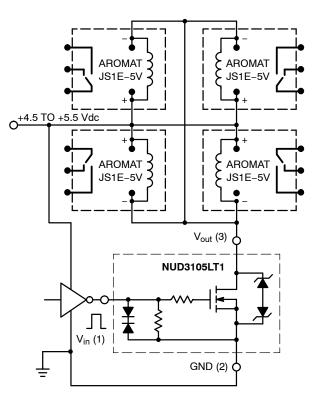
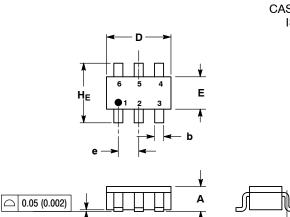


Figure 14. A Quad 5.0 V, 360 mW Coil Relay Bank



PACKAGE DIMENSIONS



Δ1

SC-74 CASE 318F-05 **ISSUE M**

NOTES:

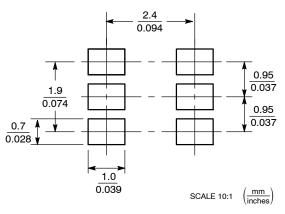
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 3
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
- OF BASE MATERIAL. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN NOM MA		
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
с	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°



5. GATE 2 6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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